

PNP - 2N6107, 2N6109, 2N6111; NPN - 2N6288, 2N6292

Complementary Silicon Plastic Power Transistors

These devices are designed for use in general-purpose amplifier and switching applications.

Features

- DC Current Gain Specified to 7.0 Amperes
 $h_{FE} = 30-150 @ I_C$
 $= 3.0 \text{ Adc} - 2N6111, 2N6288$
 $= 2.3 (\text{Min}) @ I_C = 7.0 \text{ Adc} - \text{All Devices}$
- Collector-Emitter Sustaining Voltage –
 $V_{CEO(\text{sus})} = 30 \text{ Vdc (Min)} - 2N6111, 2N6288$
 $= 50 \text{ Vdc (Min)} - 2N6109$
 $= 70 \text{ Vdc (Min)} - 2N6107, 2N6292$
- High Current Gain – Bandwidth Product
 $f_T = 4.0 \text{ MHz (Min)} @ I_C = 500 \text{ mAdc} - 2N6288, 90, 92$
 $= 10 \text{ MHz (Min)} @ I_C = 500 \text{ mAdc} - 2N6107, 09, 11$
- TO-220AB Compact Package
- Pb-Free Packages are Available*

MAXIMUM RATINGS (Note 1)

Rating	Symbol	Value	Unit
Collector-Emitter Voltage 2N6111, 2N6288 2N6109 2N6107, 2N6292	V_{CEO}	30 50 70	Vdc
Collector-Base Voltage 2N6111, 2N6288 2N6109 2N6107, 2N6292	V_{CB}	40 60 80	Vdc
Emitter-Base Voltage	V_{EB}	5.0	Vdc
Collector Current – Continuous – Peak	I_C	7.0 10	Adc
Base Current	I_B	3.0	Adc
Total Power Dissipation @ $T_C = 25^\circ\text{C}$ Derate above 25°C	P_D	40 0.32	W W/ $^\circ\text{C}$
Operating and Storage Junction Temperature Range	T_J, T_{stg}	-65 to +150	$^\circ\text{C}$

THERMAL CHARACTERISTICS

Characteristics	Symbol	Max	Unit
Thermal Resistance, Junction-to-Case	$R_{\theta JC}$	3.125	$^\circ\text{C/W}$

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

1. Indicates JEDEC Registered Data.

*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

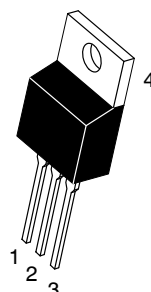


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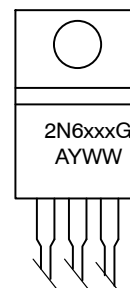
7 AMPERE POWER TRANSISTORS COMPLEMENTARY SILICON 30 – 50 – 70 VOLTS, 40 WATTS

MARKING DIAGRAM



TO-220AB
CASE 221A
STYLE 1

PIN 1. BASE
2. COLLECTOR
3. EMITTER
4. COLLECTOR



2N6xxx = Specific Device Code
xxx = See Table on Page 4
G = Pb-Free Package
A = Assembly Location
Y = Year
WW = Work Week

ORDERING INFORMATION

See detailed ordering, marking, and shipping information in the package dimensions section on page 4 of this data sheet.

PNP – 2N6107, 2N6109, 2N6111; NPN – 2N6288, 2N6292

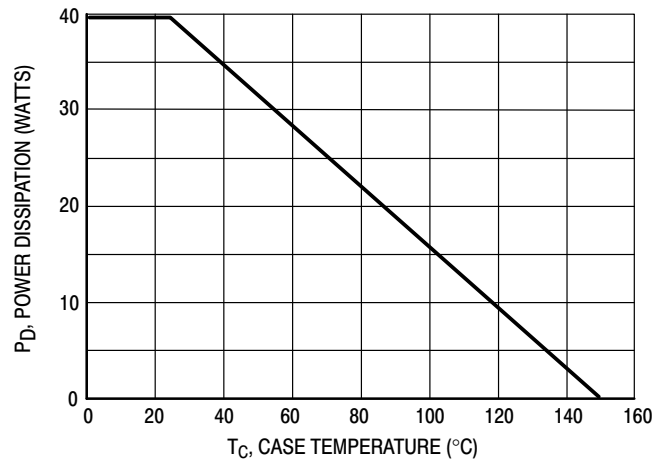


Figure 1. Power Derating

ELECTRICAL CHARACTERISTICS (T_C = 25°C unless otherwise noted) (Note 2)

Characteristic	Symbol	Min	Max	Unit
OFF CHARACTERISTICS				
Collector–Emitter Sustaining Voltage (Note 3) (I _C = 100 mAdc, I _B = 0)	V _{CEO(sus)}	30 50 70	– – –	Vdc
Collector Cutoff Current (V _{CE} = 20 Vdc, I _B = 0) (V _{CE} = 40 Vdc, I _B = 0) (V _{CE} = 60 Vdc, I _B = 0)	I _{CEO}	– – –	1.0 1.0 1.0	mAdc
Collector Cutoff Current (V _{CE} = 40 Vdc, V _{EB(off)} = 1.5 Vdc) (V _{CE} = 60 Vdc, V _{EB(off)} = 1.5 Vdc) (V _{CE} = 80 Vdc, V _{EB(off)} = 1.5 Vdc) (V _{CE} = 30 Vdc, V _{EB(off)} = 1.5 Vdc, T _C = 150°C) (V _{CE} = 50 Vdc, V _{EB(off)} = 1.5 Vdc, T _C = 150°C) (V _{CE} = 70 Vdc, V _{EB(off)} = 1.5 Vdc, T _C = 150°C)	I _{CEX}	– – – – – –	100 100 100 2.0 2.0 2.0	μAdc mAdc
Emitter Cutoff Current (V _{BE} = 5.0 Vdc, I _C = 0)	I _{EBO}	–	1.0	mAdc
ON CHARACTERISTICS (Note 3)				
DC Current Gain (I _C = 2.0 Adc, V _{CE} = 4.0 Vdc) (I _C = 2.5 Adc, V _{CE} = 4.0 Vdc) (I _C = 3.0 Adc, V _{CE} = 4.0 Vdc) (I _C = 7.0 Adc, V _{CE} = 4.0 Vdc)	h _{FE}	30 30 30 2.3	150 150 150 –	–
Collector–Emitter Saturation Voltage (I _C = 7.0 Adc, I _B = 3.0 Adc)	V _{CE(sat)}	–	3.5	Vdc
Base–Emitter On Voltage (I _C = 7.0 Adc, V _{CE} = 4.0 Vdc)	V _{BE(on)}	–	3.0	Vdc
DYNAMIC CHARACTERISTICS				
Current Gain — Bandwidth Product (Note 4) (I _C = 500 mAdc, V _{CE} = 4.0 Vdc, f _{test} = 1.0 MHz)	f _T	4.0 10	– –	MHz
Output Capacitance (V _{CB} = 10 Vdc, I _E = 0, f = 1.0 MHz)	C _{ob}	–	250	pF
Small–Signal Current Gain (I _C = 0.5 Adc, V _{CE} = 4.0 Vdc, f = 50 kHz)	h _{fe}	20	–	–

2. Indicates JEDEC Registered Data.

3. Pulse Test: Pulse Width ≤ 300 μs, Duty Cycle ≤ 2.0%.

4. f_T = |h_{fe}| • f_{test}

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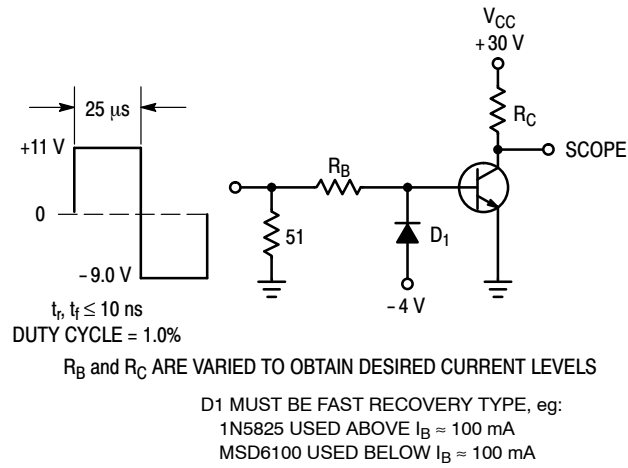


Figure 2. Switching Time Test Circuit

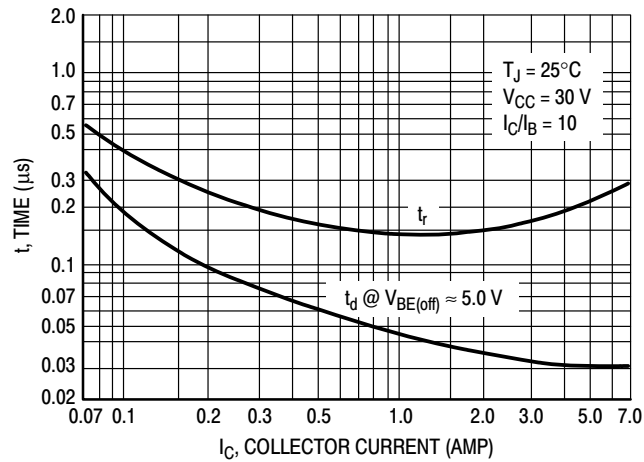


Figure 3. Turn-On Time

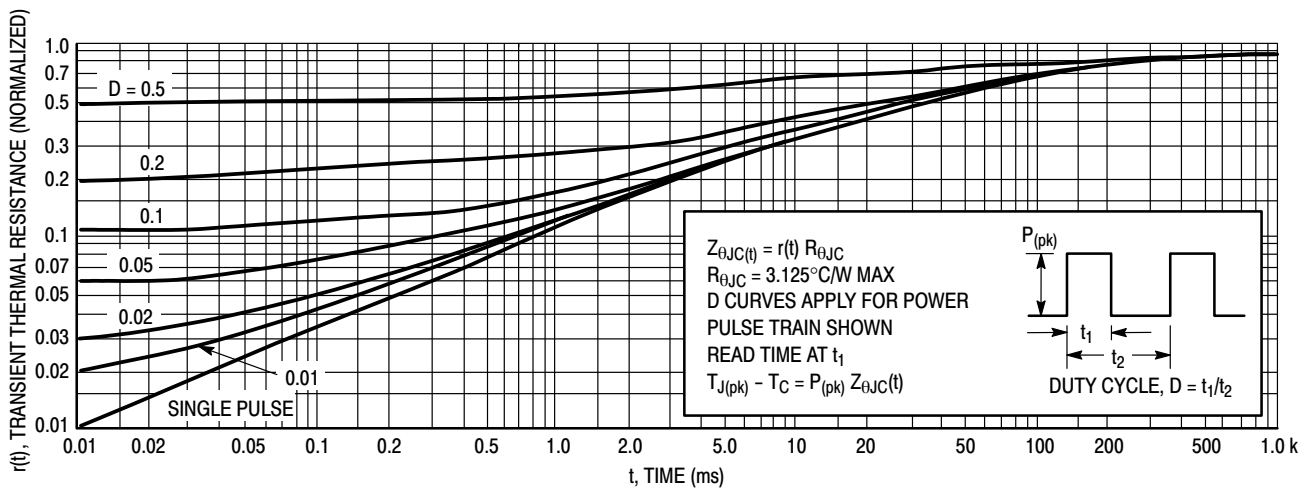


Figure 4. Thermal Response

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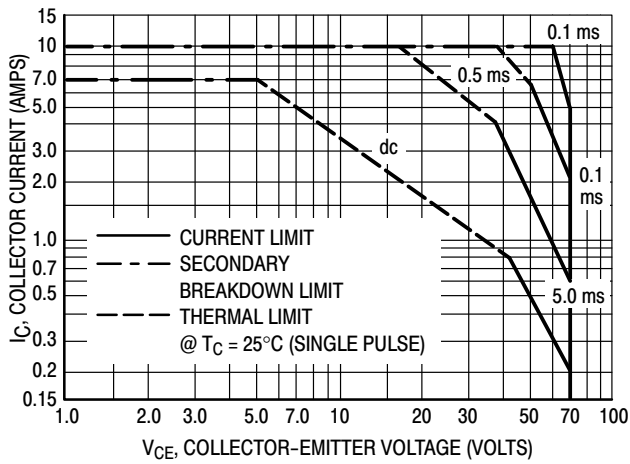


Figure 5. Active-Region Safe Operating Area

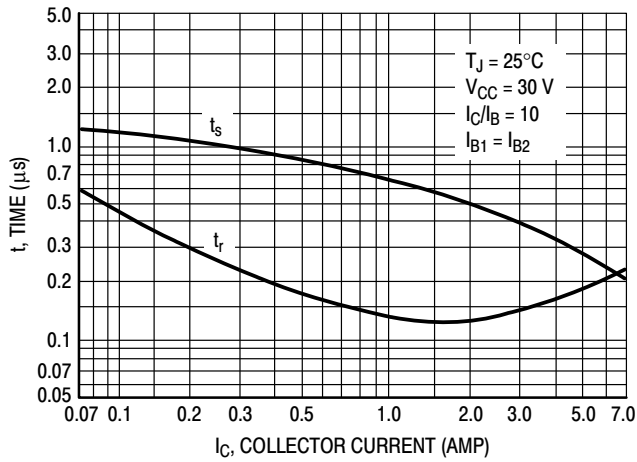


Figure 6. Turn-Off Time

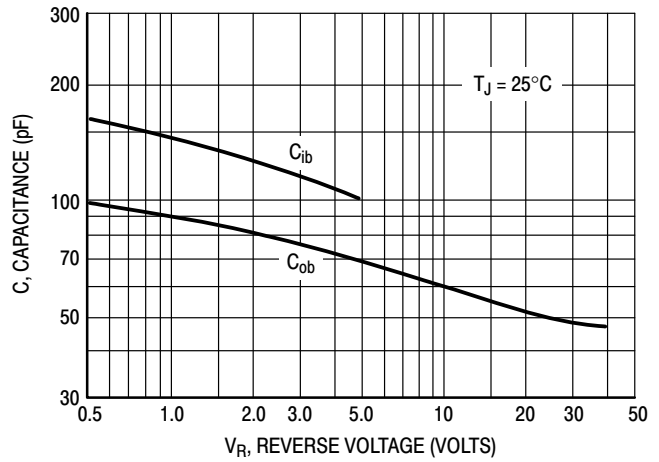


Figure 7. Capacitance

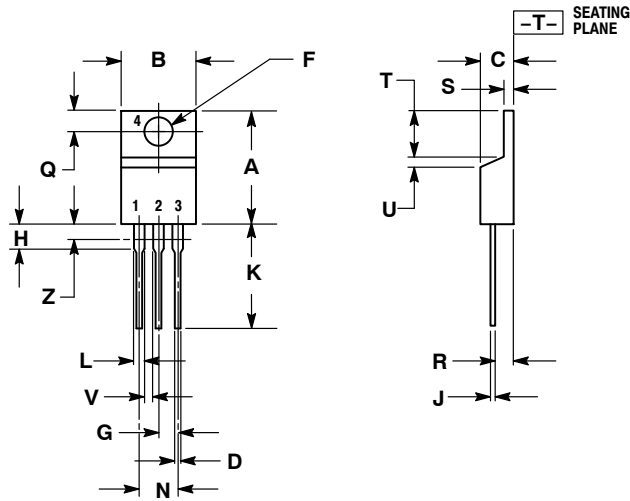
ORDERING INFORMATION

Device	Device Marking	Package	Shipping
2N6107	2N6107	TO-220AB	50 Units / Rail
2N6107G		TO-220AB (Pb-Free)	
2N6109	2N6109	TO-220AB	50 Units / Rail
2N6109G		TO-220AB (Pb-Free)	
2N6111	2N6111	TO-220AB	50 Units / Rail
2N6111G		TO-220AB (Pb-Free)	
2N6288	2N6288	TO-220AB	50 Units / Rail
2N6288G		TO-220AB (Pb-Free)	
2N6292	2N6292	TO-220AB	50 Units / Rail
2N6292G		TO-220AB (Pb-Free)	

PNP – 2N6107, 2N6109, 2N6111; NPN – 2N6288, 2N6292

PACKAGE DIMENSIONS

TO-220 CASE 221A-09 ISSUE AG



NOTES:

1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: INCH.
3. DIMENSION Z DEFINES A ZONE WHERE ALL BODY AND LEAD IRREGULARITIES ARE ALLOWED.

DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.570	0.620	14.48	15.75
B	0.380	0.405	9.66	10.28
C	0.160	0.190	4.07	4.82
D	0.025	0.036	0.64	0.91
F	0.142	0.161	3.61	4.09
G	0.095	0.105	2.42	2.66
H	0.110	0.161	2.80	4.10
J	0.014	0.025	0.36	0.64
K	0.500	0.562	12.70	14.27
L	0.045	0.060	1.15	1.52
N	0.190	0.210	4.83	5.33
Q	0.100	0.120	2.54	3.04
R	0.080	0.110	2.04	2.79
S	0.045	0.055	1.15	1.39
T	0.235	0.255	5.97	6.47
U	0.000	0.050	0.00	1.27
V	0.045	---	1.15	---
Z	---	0.080	---	2.04

STYLE 1:

1. BASE
2. COLLECTOR
3. EMITTER
4. COLLECTOR

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Офис по работе с юридическими лицами:

105318, г.Москва, ул.Щербаковская д.3, офис 1107, 1118, ДЦ «Щербаковский»

Телефон: +7 495 668-12-70 (многоканальный)

Факс: +7 495 668-12-70 (доб.304)

E-mail: info@moschip.ru

Skype отдела продаж:

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